TOSHIBA

TOSHIBA Photocoupler GaAłAs Ired & Photo IC

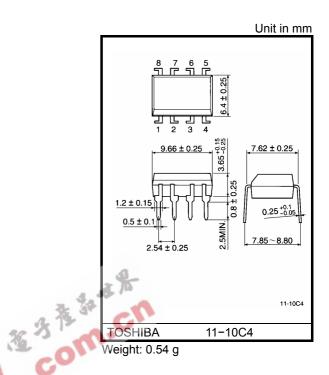
TLP2630

Digital Logic Isolation Tele–Communication Analog Data Equipment Control Microprocessor System Interface

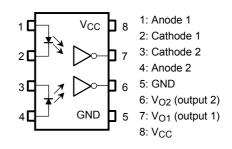
The TOSHIBA TLP2630 dual photocoupler consists of a pair of GaAlAs light emitting diode and integrated high gain, high speed photodetector. The output of the detector circuit is an open collector,

schottky clamped transistor. This unit is 8–lead DIP.

- Input current threshold: $I_F = 5mA(max.)$
- LSTTL/TTL compatible: 5V supply
- Switching speed: 10MBd(typ.)
- Guaranteed performance over temperature: $0 \sim 70^{\circ}$ C
- Isolation voltage: 2500V_{rms}(min.)
- UL recognized:UL1577, file no. E67349



Pin Configuration (top view)

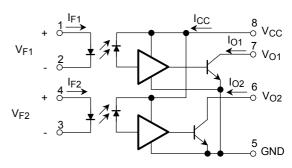


Truth Table (positive logic)

Input	Output
Н	L
L	Н

A 0.01 to 0.1 μF bypass capacitor must connected between pins 8 and 5 (see Note 1).

Schematic



Absolute Maximum Ratings (no derating required up to 70°C)

	Characteristic	Symbol	Rating	Unit
	Forward current(each channel)	١ _F	20	mA
LED	Forward current(each channel) Pulse forward current (each channel)* Reverse voltage(each channel) Output current(each channel) Output voltage(each channel) Supply voltage (1 minute maximum) Output collector power dissipation(each channel) ating temperature range ge temperature range soldering temperature (10 s)	I _{FP}	FP 30	
	Reverse voltage(each channel)	VR	5	V
	Output current(each channel)	Ι _Ο	16	mA
tecto	Output voltage(each channel)	Vo	-0.5~7	V
		V _{CC}	7	V
		PO	40	mW
Oper	ating temperature range	T _{stg}	-55~125	°C
Stora	ge temperature range	T _{opr}		
Lead	Idering temperature (10 s) (Note 1) T _{sol} 260		°C	
Isolat	tion voltage (AC, 1 min., R.H.≤ 60%, Note 3)	BVS	2500	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

* t \leq 1 msec duration.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Input current, low level, each channel	I _{FL}	0	_	250	μA
Input current, high level, each channel	I _{FH}	6.3*	_	15	mA
Supply voltage**, output	V _{CC}	4.5	5	5.5	V
Fan out(TTL load, each channel)	N	_	_	8	
Operating temperature	T _{opr}	0		70	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

* 6.3mA is a guard banded value which allows for at least 20% CTR degradation. Initial input current threshold value is 5.0mA or less.

**This item denotes operating ranges, not meaning of recommended operating conditions.

Electrical Characteristics (Ta = 0~70°C, unless otherwise noted)

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Characteristic	Symbol	Test Condition	Min.	Тур.*	Max.	Unit	
Input forward voltage (each channel)	VF	I _F = 10mA, Ta = 25°C		1.65	1.75	V	
Input diode temperature coefficient(each channel)	ΔV _F / ΔTa	I _F = 10mA		-2.0	_	mV / °C	
Input reverse breakdown voltage(each channel)	BV _R	I _R = 10μΑ, Ta = 25°C	5	—	—	V	
Input capacitance (each channel)	CT	V _F = 0, f = 1MHz		45		pF	
High level output current (each channel)	I _{OH}	V _{CC} = 5.5V, V _O = 5.5V I _F = 250µA		1	250	μA	
Low level output voltage (each channel)	V _{OL}	V _{CC} = 5.5V, I _F = 5mA I _{OL} (sinking) = 13mA		0.4	0.6	V	
High level supply current (both channels)	Іссн	V _{CC} = 5.5V, I _F = 0		14	30	mA	
Low level supply current (both channels)	ICCL	V _{CC} = 5.5V, I _F = 10mA		24	36	mA	
Isolation voltage	R _S	V _S = 500V, R.H.≤ 60% (Note 3)	_	10 ¹⁴	_	Ω	
Capacitance(input-output)	CS	f = 1MHz (Note 3)	_	0.6	_	pF	
Input-input leakage current	I _{I-I}	R.H.≤ 60%, t = 5s V _{I-I} = 500V (Note 6)	-	0.005	_	μA	
Resistance(input-input)	R _{I–I}	V _{I-I} = 500V (Note 6)	15-	10 ¹¹	_	Ω	
Capacitance(input-input)	C _{I–I}	f = 1MHz (Note 6)	-	0.25	_	pF	
Capacitance(input-input) C_{I-I} f = 1MHz (Note 6) 0.25 $ pF$ * All typical values are at V_{CC} = 5V, Ta = 25°C. • </td							

Switching Characteristics (Ta =25°C , V_{CC}=5V)

Characteristic	Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time to low output level	t _{pHL}	1	$I_F = 0 \rightarrow 7.5 \text{mA}, R_L = 350\Omega$ $C_L = 15 \text{pF}$ (each channel)		60	75	ns
Propagation delay time to high output level	t _{pLH}	1	$I_F = 7.5 \text{mA} \rightarrow 0$, $R_L = 350 \Omega$ $C_L = 15 \text{pF}$ (each channel)	_	60	75	ns
Output rise a time,output fall time(10~90%)	t _r ,t _f	1	$I_F = 0 \overrightarrow{\leftarrow} 7.5 \text{mA}, R_L = 350 \Omega$ $C_L = 15 pF$ (each channel)	_	30	_	ns
Common mode transient immunity at high output level	CM _H	2	$\label{eq:lf} \begin{array}{l} I_{F} = 0, \ R_{L} = 350\Omega \\ V_{CM} = 200V \\ V_{O}(min.) = 2V \\ (each channel, Note 4) \end{array}$		200		V / µs
Common mode transient immunity at low output level	CML	2	$\begin{array}{l} {\sf I}_{\sf F} = 7.5 m {\sf A}, {\sf R}_{\sf L} = 350 \Omega \\ {\sf V}_{\sf CM} = 200 {\sf V} \\ {\sf V}_{\sf O}(max.) = 0.8 {\sf V} \\ \qquad $	_	-500	_	V / µs

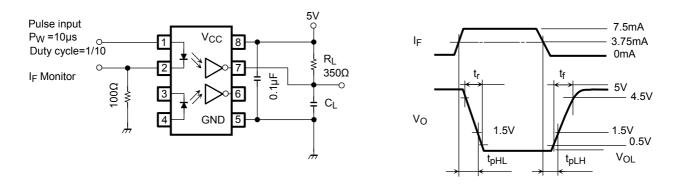
(Note 1) 2mm below seating plane.

- (Note 2) The V_{CC} supply voltage to each TLP2630 isolator must be bypassed by a 0.01µF capacitor or larger. This can be either a ceramic or solid tantalum capacitor with good high frequency characteristic and should be connected as close as possible to the package V_{CC} and GND pins each device.
- (Note 3) Device considered a two-terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.
- (Note 4) CM_H·the maximum tolerable rate of rise of the common mode voltage to ensure the output will remain in the high state(i.e., V_{OUT} > 2.0V)
- (Note 5) CM_L · the maximum tolerable rate of fall of the common mode voltage to ensure the output will remain in the low output state(i.e., V_{OUT} > 0.8V)
 - Measured in volts per microsecond $(V / \mu s)$.

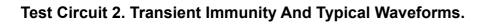
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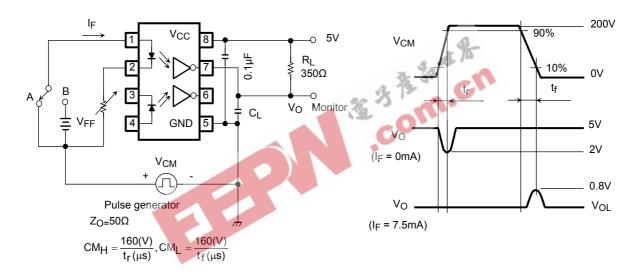
(Note 6) Measured between pins 1 and 2 shorted together, and pins 3 and 4 shorted together.

Test Circuit 1. t_{pHL} And t_{pLH}



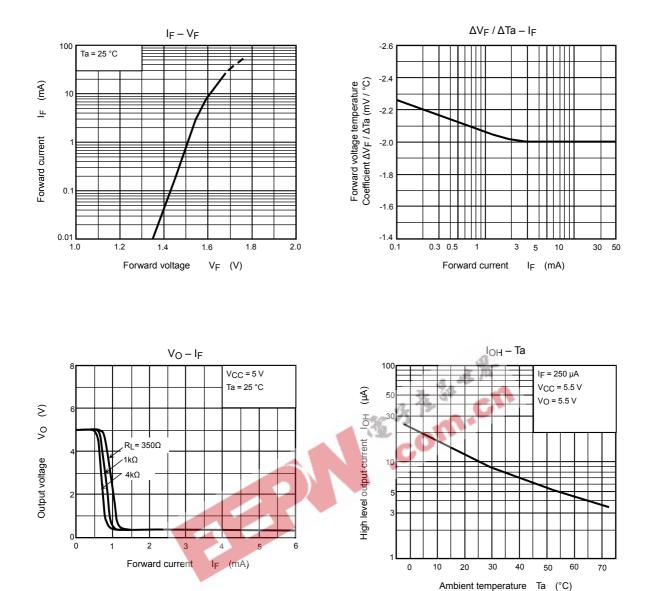
* C_L is approximately 15pF which includes probe and stray wirng capacitance.

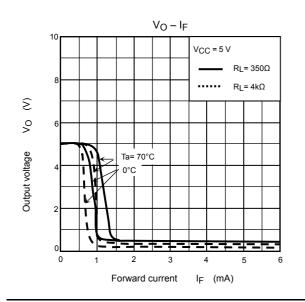


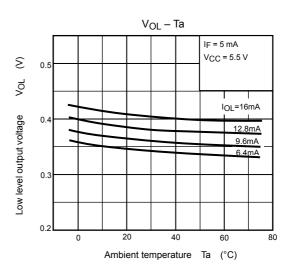


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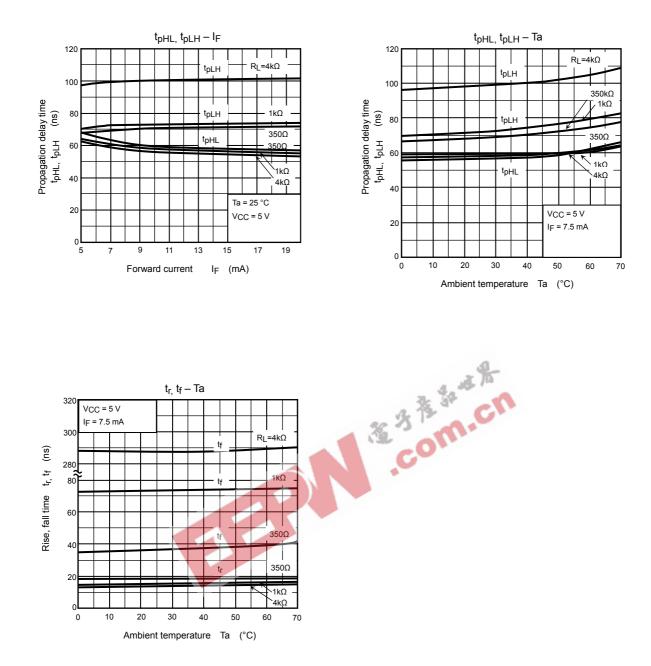
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